ABSOLUTE MAXIMUM RATINGS

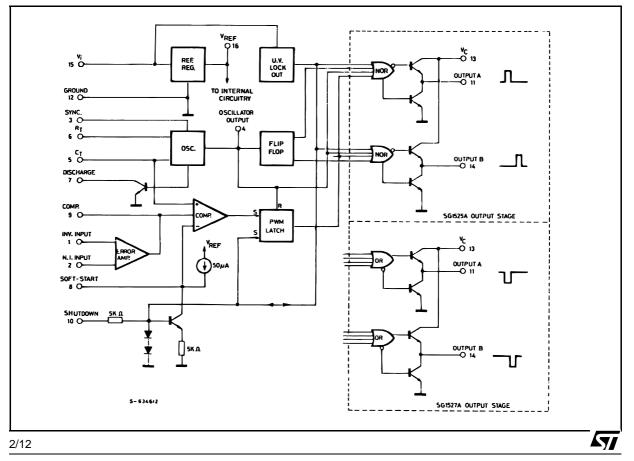
Symbol	Parameter	Value	Unit
Vi	Supply Voltage	40	V
Vc	Collector Supply Voltage	40	V
losc	Oscillator Charging Current	5	mA
lo	Output Current, Source or Sink	500	mA
I _R	Reference Output Current	50	mA
Ι _Τ	Current through C _T Terminal Logic Inputs Analog Inputs	5 – 0.3 to + 5.5 – 0.3 to V _i	mA V V
P _{tot}	Total Power Dissipation at T _{amb} = 70 °C	1000	mW
Tj	Junction Temperature Range	– 55 to 150	°C
T _{stg}	Storage Temperature Range	– 65 to 150	°C
T _{op}	Operating Ambient Temperature : SG2525A SG3525A	– 25 to 85 0 to 70	လို လိ

THERMAL DATA

Symbol	Parameter	SO16	DIP16	Unit
R _{th j-pins}	Thermal Resistance Junction-pins Max		50	°C/W
R _{th j-amb}	Thermal Resistance Junction-ambient Max		80	°C/W
R _{th} j-alumina	Thermal Resistance Junction-alumina (*) Max	50		°C/W

* Thermal resistance junction-alumina with the device soldered on the middle of an alumina supporting substrate measuring 15 × 20 mm; 0.65 mm thickness with infinite heatsink.

BLOCK DIAGRAM



ELECTRICAL CHARACTERISTICS (V# i = 20 V, and over operating temperature, unless otherwise specified)

Sumbal	Baramatar	Test Conditions	S	G2525	A	5	G3525	A	110-14
Symbol	ool Parameter Test Conditions		Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
REFEREN	CE SECTION	•							•
V_{REF}	Output Voltage	T _j = 25 °C	5.05	5.1	5.15	5	5.1	5.2	V
ΔV_{REF}	Line Regulation	V _i = 8 to 35 V		10	20		10	20	mV
ΔV_{REF}	Load Regulation	$I_L = 0$ to 20 mA		20	50		20	50	mV
$\Delta V_{REF} / \Delta T^*$	Temp. Stability	. Stability Over Operating Range		20	50		20	50	mV
*	Total Output Variation	Line, Load and Temperature	5		5.2	4.95		5.25	V
	Short Circuit Current	$V_{REF} = 0 T_j = 25 \ ^{\circ}C$		80	100		80	100	mA
*	Output Noise Voltage	10 Hz \leq f \leq 10 kHz, T _j = 25 °C		40	200		40	200	μVrms
ΔV_{REF}^*	Long Term Stability	$T_j = 125 \ ^{\circ}C, \ 1000 \ hrs$		20	50		20	50	mV
OSCILLAT	OR SECTION * *								
*, ●	Initial Accuracy	T _j = 25 °C		± 2	± 6		± 2	± 6	%
*, ●	Voltage Stability	V _i = 8 to 35 V		± 0.3	± 1		± 1	± 2	%
$\Delta f / \Delta T^*$	Temperature Stability	Over Operating Range		± 3	± 6		± 3	± 6	%
f _{MIN}	Minimum Frequency	R_T = 200 K Ω C_T = 0.1 μ F			120			120	Hz
f _{MAX}	Maximum Frequency	$R_T = 2 \text{ K}\Omega \text{ C}_T = 470 \text{ pF}$	400			400			KHz
	Current Mirror	I _{RT} = 2 mA	1.7	2	2.2	1.7	2	2.2	mA
*, ●	Clock Amplitude		3	3.5		3	3.5		V
*, ●	Clock Width	T _j = 25 °C	0.3	0.5	1	0.3	0.5	1	μs
	Sync Threshold		1.2	2	2.8	1.2	2	2.8	V
	Sync Input Current	Sync Voltage = 3.5 V		1	2.5		1	2.5	mA
ERROR A	MPLIFIER SECTION (Vcr	_и = 5.1 V)							
Vos	Input Offset Voltage			0.5	5		2	10	mV
l _b	Input Bias Current			1	10		1	10	μΑ
l _{os}	Input Offset Current				1			1	μΑ
	DC Open Loop Gain	$R_L \ge 10 \ M\Omega$	60	75		60	75		dB
*	Gain Bandwidth Product	$G_v = 0 \ dB$ $T_j = 25 \ ^\circ C$	1	2		1	2		MHz
*,∎	DC Transconduct.	$\begin{array}{l} 30 \ \text{K}\Omega \leq \text{R}_{\text{L}} \leq 1 \ \text{M}\Omega \\ \text{T}_{\text{j}} = 25 \ ^{\circ}\text{C} \end{array}$	1.1	1.5		1.1	1.5		ms
	Output Low Level			0.2	0.5		0.2	0.5	V
	Output High Level		3.8	5.6		3.8	5.6		V
CMR	Comm. Mode Reject.	V _{CM} = 1.5 to 5.2 V	60	75		60	75		dB
PSR	Supply Voltage Rejection	$V_i = 8 \text{ to } 35 \text{ V}$	50	60		50	60		dB

Symbol	Parameter	Test Conditions	SG2525A			SG3525A			Unit
Symbol Parameter		Mi		Тур.	Max.	Min.	Тур.	Max.	Unit
	MPARATOR	•							
	Minimum Duty-cycle				0			0	%
٠	Maximum Duty-cycle		45	49		45	49		%
٠	Input Threshold	Zero Duty-cycle	0.7	0.9		0.7	0.9		V
		Maximum Duty-cycle		3.3	3.6		3.3	3.6	V
*	Input Bias Current			0.05	1		0.05	1	μA
SHUTDO	WN SECTION								
	Soft Start Current	$V_{SD} = 0 V, V_{SS} = 0 V$	25	50	80	25	50	80	μA
	Soft Start Low Level	V _{SD} = 2.5 V		0.4	0.7		0.4	0.7	V
	Shutdown Threshold	To outputs, $V_{SS} = 5.1 \text{ V}$ T _j = 25 °C	0.6	0.8	1	0.6	0.8	1	V
	Shutdown Input Current	V _{SD} = 2.5 V		0.4	1		0.4	1	mA
*	Shutdown Delay	V_{SD} = 2.5 V T _j = 25 °C		0.2	0.5		0.2	0.5	μs
OUTPUT	DRIVERS (each output) (V _C = 20 V)							
	Output Low Level	I _{sink} = 20 mA		0.2	0.4		0.2	0.4	V
		I _{sink} = 100 mA		1	2		1	2	V
	Output High Level	I _{source} = 20 mA	18	19		18	19		V
		I _{source} = 100 mA	17	18		17	18		V
	Under-Voltage Lockout	V_{comp} and V_{ss} = High	6	7	8	6	7	8	V
Ιc	Collector Leakage	V _C = 35 V			200			200	μΑ
t _r *	Rise Time	C _L = 1 nF, T _j = 25 °C		100	600		100	600	ns
t _f *	Fall Time	C _L = 1 nF, T _j = 25 °C		50	300		50	300	ns
TOTAL S	TANDBY CURRENT								
ls	Supply Current	V _i = 35 V		14	20		14	20	mA

ELECTRICAL CHARACTERISTICS (continued)

* These parameters, although guaranteed over the recommended operating conditions, are not 100 % tested in production.

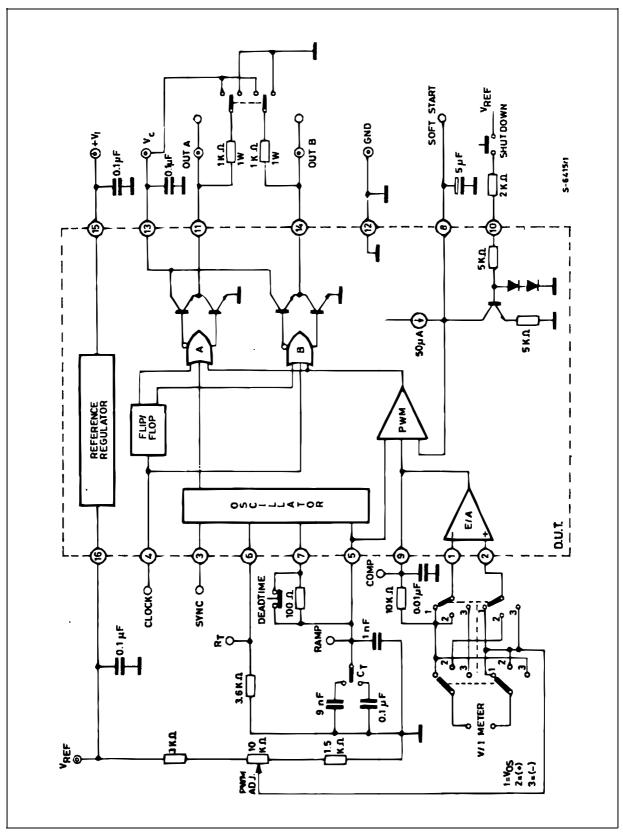
• Tested at f_{osc} = 40 KHz (R_T = 3.6 K Ω , C_T = 10nF, R_D = 0 Ω). Approximate oscillator frequency is defined by :

$$f = \frac{1}{C_{T} (0.7 R_{T} + 3 R_{D})}$$

■ DC transconductance (g_M) relates to DC open-loop voltage gain (G_v) according to the following equation : $G_v = g_M R_L$ where R_L is the resistance from pin 9 to ground. The minimum g_M specification is used to calculate minimum G_v when the error amplifier output is loaded.

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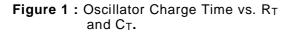
TEST CIRCUIT

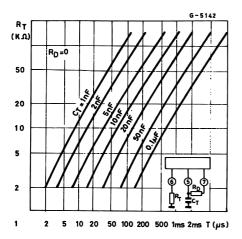


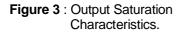
RECOMMENDED OPERATING CONDITIONS (•)

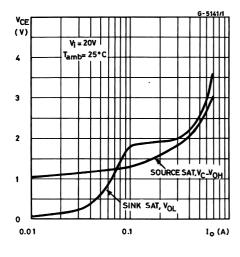
Parameter	Value
Input Voltage (Vi)	8 to 35 V
Collector Supply Voltage (V _C)	4.5 to 35 V
Sink/Source Load Current (steady state)	0 to 100 mA
Sink/Source Load Current (peak)	0 to 400 mA
Reference Load Current	0 to 20 mA
Oscillator Frequency Range	100 Hz to 400 KHz
Oscillator Timing Resistor	2 KΩ to 150 KΩ
Oscillator Timing Capacitor	0.001 μF to 0.1 μF
Dead Time Resistor Range	0 to 500 Ω

(•) Range over which the device is functional and parameter limits are guaranteed.









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Figure 2 : Oscillator Discharge Time vs. R_D and C_T .

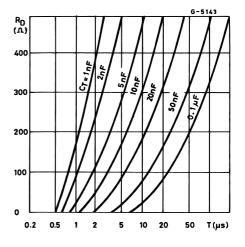


Figure 4 : Error Amplifier Voltage Gain and Phase vs. Frequency.

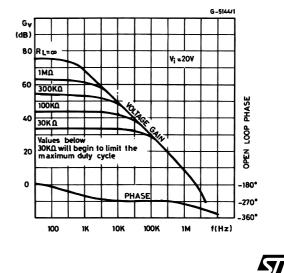
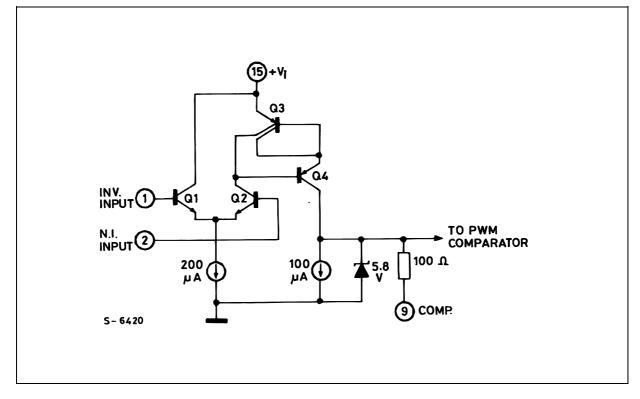


Figure 5 : Error Amplifier.



PRINCIPLES OF OPERATION

SHUTDOWN OPTIONS (see Block Diagram)

Since both the compensation and soft-start terminals (Pins 9 and 8) have current source pull-ups, either can readily accept a pull-down signal which only has to sink a maximum of $100 \,\mu$ A to turn off the outputs. This is subject to the added requirement of discharging whatever external capacitance may be attached to these pins.

An alternate approach is the use of the shutdown circuitry of Pin 10 which has been improved to enhance the available shutdown options. Activating this circuit by applying a positive signal on Pin 10 performs two functions : the PWM latch is immediately set providing the fastest turn-off signal to the outputs ; and a 150 μA current sink begins to discharge the external soft-start capacitor. If the shutdown command is short, the PWM signal is terminated without significant discharge of the soft-start capacitor, thus, allowing, for example, a convenient implementation of pulse-by-pulse current limiting. Holding Pin 10 high for a longer duration, however, will ultimately discharge this external capacitor, recycling slow turn-on upon release.

Pin 10 should not be left floating as noise pickup could conceivably interrupt normal operation.

Figure 6 : Oscillator Schematic.

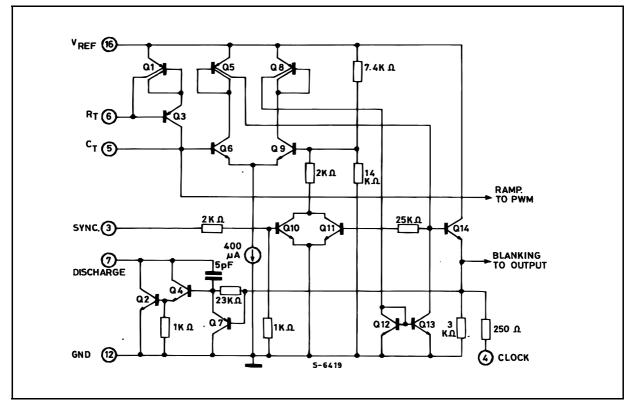


Figure 7 : Output Circuit (1/2 circuit shown).

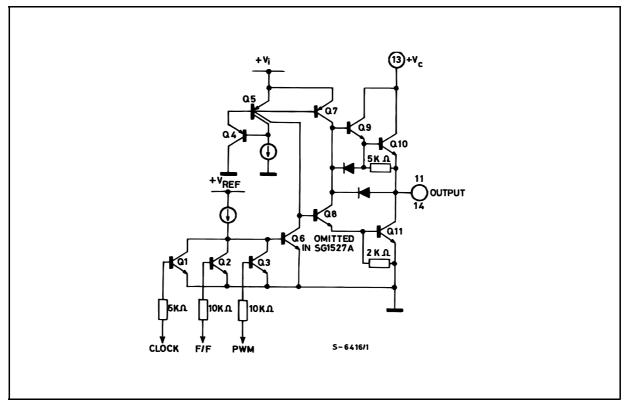
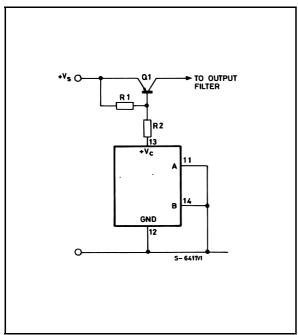


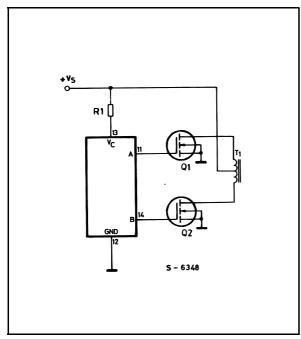


Figure 8.



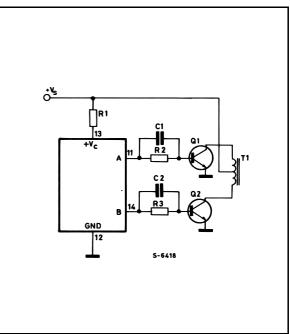
For single-ended supplies, the driver outputs are grounded. The V_C terminal is switched to ground by the totem-pole source transistors on alternate oscillator cycles.

Figure 10.



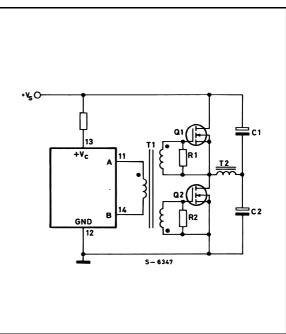
The low source impedance of the output drivers provides rapid charging of Power Mos input capacitance while minimizing external components.

Figure 9.



In conventional push-pull bipolar designs, forward base drive is controlled by $R_1 - R_3$. Rapid turn-off times for the power devices are achieved with speed-up capacitors C_1 and C_2 .

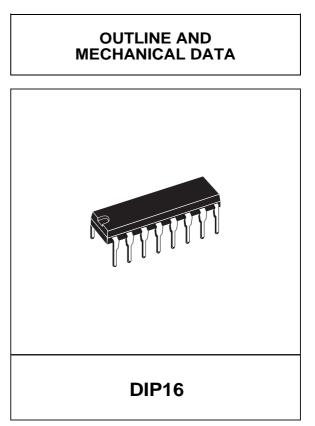
Figure 11.

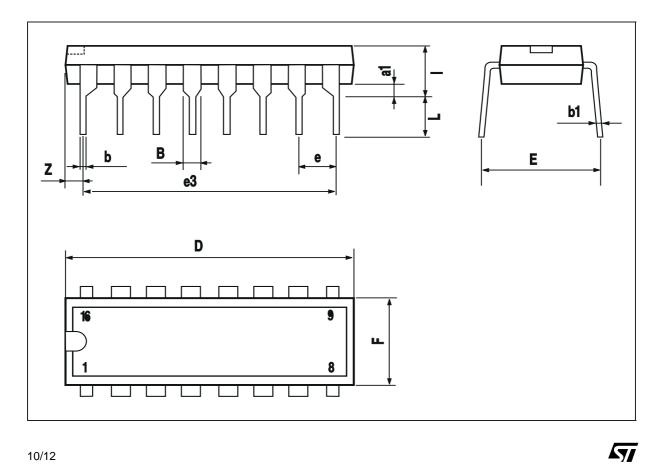


Low power transformers can be driven directly. Automatic reset occurs during dead time, when both ends of the primary winding are switched to ground.



DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
е		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
Ι			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050

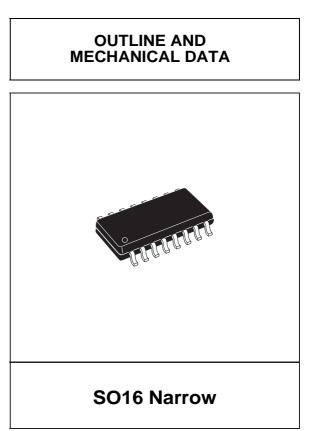




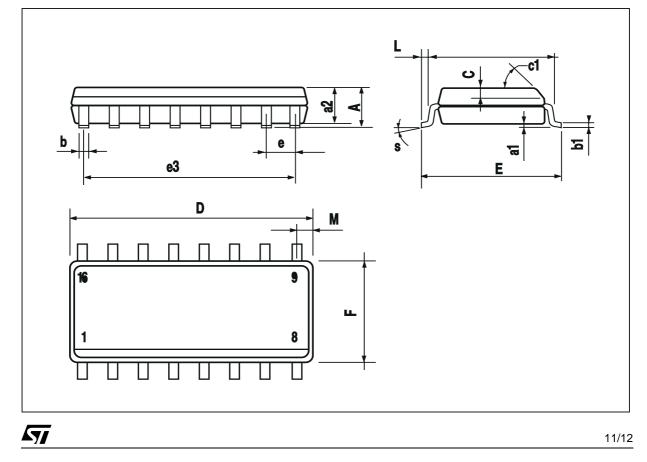
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DIM.		mm			inch			
Dini.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			1.75			0.069		
a1	0.1		0.25	0.004		0.009		
a2			1.6			0.063		
b	0.35		0.46	0.014		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.020			
c1			45° (typ.)				
D (1)	9.8		10	0.386		0.394		
Е	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F (1)	3.8		4	0.150		0.157		
G	4.6		5.3	0.181		0.209		
L	0.4		1.27	0.016		0.050		
М			0.62			0.024		
S	8°(max.)							



(1) D and F do not include mold flash or protrusions. Mold flash or potrusions shall not exceed 0.15mm (.006inch).



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